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SIMPLIFIED HIGH Q INDUCTOR SUBSTRATE

Abstract

The present invention provides for a method of manufacturing a simplified high Q inductor substrate and a semiconductor device having that substrate. The method for manufacturing the simplified high Q inductor substrate preferably comprises forming a base substrate over a semiconductor wafer, wherein the base substrate has a given dopant concentration and then forming an epitaxial (EPI) layer over the base substrate. The EPI layer includes epitaxially forming a first doped region in the EPI layer over the base substrate and then epitaxially forming a second doped region in the EPI layer over the first doped region. The first doped region has a dopant concentration greater than the given dopant concentration of the base substrate, and the second doped region has a dopant concentration less than the first doped region.

(**Figure 3**)



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